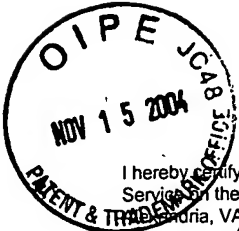


10-66842

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CERTIFICATE OF MAILING

I hereby certify that this paper (along with any paper or item referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below with sufficient postage as first-class mail in an envelope addressed to Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450.

Date: 11/10/04

Janet Parr
Janet Parr

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent No.: 6,812,514 *B1*
Applicant: Yang et al.
Issue Date: November 2, 2004
For: HIGH DENSITY FLOATING GATE FLASH MEMORY AND
FABRICATION PROCESSES THEREFOR
Docket No. H0462A

**REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT
FOR PTO MISTAKE (37 CFR 1.322(a))**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Attention: Decision and Certificate of Correction
Branch of the Patent Issue Division

Certificate
NOV 23 2004
of Correction

Sir:

Request is made for issuance of a certificate of correction to correct PTO mistakes in the printing of the subject patent. Attached hereto in duplicate is form PTO/SB/44 with at least one copy being suitable for printing.

The exact pages and line numbers in the application where the correct language is found are:

For the correction at column 7, line 31, the correct language can be found in the application at page 10, line 8.

For the correction at column 7, line 35, the correct language can be found in the application at page 10, line 11.

NOV 23 2004

For the correction at column 9, line 30, the correct language can be found in the application at page 13, line 3.

For the correction at column 9, line 59, the correct language can be found in the application at page 13, line 23..

For the correction at column 11, line 66, the correct language can be found in the application at page 16, line 20.

For the correction at column 12, line 33, the correct language can be found in the application at page 17, line 11.

For the correction at column 12, line 39, the correct language can be found in the application at page 17, line 15.

For the correction at column 12, line 48, the correct language can be found in the application at page 17, line 21.

For the correction at column 12, line 61, the correct language can be found in the application at page 17, line 28.

For the correction at column 15, line 22, the correct language can be found in the application at page 21, line 7.

For the correction at column 21, line 13, the correct language can be found in the application at page 29, line 18.

For the correction at column 22, claim 1, lines 9-10, the correct language can be found in the application at page 32, claim 1, lines 7-8.

For the correction at column 24, claim 20, lines 2, the correct language can be found in the application at page 35, claim 1, lines 7-8.

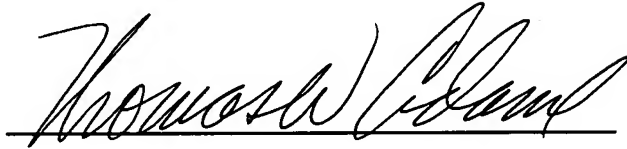
Please send the Certificate to:

RENNER, OTTO, BOISSELLE & SKLAR, LLP
1621 Euclid Avenue – Nineteenth Floor
Cleveland, OH 44115

No fee is believed to be necessary.

Respectfully submitted,

RENNER, OTTO, BOISSELLE & SKLAR, LLP

A handwritten signature in cursive script, appearing to read "Thomas W. Adams", is written over a horizontal line.

Thomas W. Adams
Reg. No. 35,047

1621 Euclid Avenue
Nineteenth Floor
Cleveland, OH 44115

(216) 621-1113

NOV 23 2004

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,812,514 **61**

DATED : November 2, 2004

INVENTOR(S) : Yang et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 7, Line 31, replace "high-K; dielectric" with --high-K dielectric--

Column 7, Line 35, replace "may be!" with --may be--

Column 9, Line 30, replace "describe.d" with --described--

Column 9, Line 59, replace "and or" with --and/or--

Column 11, Line 66, replace "thereof Silicon" with --thereof. Silicon--

Column 12, Line 33, replace "mark" with --mask--

Column 12, Line 39, replace "an isotropic" with --an anisotropic--

Column 12, Line 48, replace "leave structure" with --leave structures--

Column 12, Line 61, replace "embodiments an" with --embodiment, an--

Column 15, Line 22, replace "as.that" with --as that--

Column 21, Line 13, replace "to density the" with --to densify the--

Column 22, Claim 1, Lines 9-10, replace "hard spacers" with --hard mask spacers--

Column 24, Claim 20, Line 2, replace "structure" with --structures--

MAILING ADDRESS OF SENDER:

Renner, Otto, Boisselle & Sklar, LLP
1621 Euclid Avenue, Nineteenth Floor
Cleveland, OH 44115

PATENT NO. 6,812,514

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This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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NOV 23 2004

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,812,514 **81**
 DATED : November 2, 2004
 INVENTOR(S) : Yang et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 7, Line 31, replace "high-K; dielectric" with --high-K dielectric--

Column 7, Line 35, replace "may be!" with --may be--

Column 9, Line 30, replace "describe.d" with --described--

Column 9, Line 59, replace "and or" with --and/or--

Column 11, Line 66, replace "thereof Silicon" with --thereof. Silicon--

Column 12, Line 33, replace "mark" with --mask--

Column 12, Line 39, replace "an isotropic" with --an anisotropic--

Column 12, Line 48, replace "leave structure" with --leave structures--

Column 12, Line 61, replace "embodiments an" with --embodiment, an--

Column 15, Line 22, replace "as.that" with --as that--

Column 21, Line 13, replace "to density the" with --to densify the--

Column 22, Claim 1, Lines 9-10, replace "hard spacers" with --hard mask spacers--

Column 24, Claim 20, Line 2, replace "structure" with --structures--

MAILING ADDRESS OF SENDER:

Renner, Otto, Boisselle & Sklar, LLP
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PATENT NO. 6,812,514

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